IN THE CLAIMS:

Please amend claim 1 and add new claims 7-23 as follows.

- (Currently Amended) A semiconductor device comprising: 1.
- a substrate having a main surface including a first area, a second area surrounding the first area, and a third area surrounding the second area;
- a first insulating protective film that is provided in on the first area and formed in a shape having no angles;

a second insulating protective film provided in on the third area;

a die bonding layer formed on the first insulating protective film and the second area of the substrate;

a semiconductor chip that is provided on the die bonding layer first insulating protective film and has a bottom surface facing to the die bonding layer first insulating protective film; and

a sealing resin covering the semiconductor chip,

wherein the bottom surface of the semiconductor chip covers the first area and a part of the second area.

- (Canceled) 2.-6.
- (New) The semiconductor device according to claim 1, wherein the 7. semiconductor has a first rectangular shape, the first area has a second rectangular shape that is smaller than the first rectangular shape and the second area has a predetermined width.
- (New) The semiconductor device according to claim 1, wherein the substrate 8. has a plurality of interconnections locating from the first area to the third area through the second area.
- (New) The semiconductor device according to claim 8, wherein the substrate 9. further has a plurality of bonding pads connected to the interconnections.

- 10. (New) The semiconductor device according to claim 9, wherein the bonding pads are located on the third area.
- 11. (New) The semiconductor device according to claim 8, wherein the substrate further has a plurality of through holes connected to the interconnections.
- 12. (New) The semiconductor device according to claim 11, wherein the through holes are located on the first area.
- 13. (New) The semiconductor device according to claim 1, wherein the substrate has a back surface opposite to the main surface and wherein the substrate has a plurality of conductive terminals located on the back side of the substrate.
- 14. (New) The semiconductor device according to claim 13, wherein the conductive terminals are solder balls.
 - (New) A semiconductor device comprising:

a substrate having a main surface including a first area, a second area surrounding the first area, and a third area surrounding the second area, and a back surface opposite to the main surface;

an insulating protective film formed on a part of the first area and the third area;

a die bonding layer formed on the first insulating protective film and a part of the second area of the substrate;

a semiconductor chip formed on the die bonding layer, the die bonding layer having a top surface and a bottom surface opposite to the top surface and facing the die bonding layer; and

a sealing resin covering the semiconductor chip,

wherein the semiconductor chip is located over the first area and a part of the second area.

- (New) The semiconductor device according to claim 15, wherein the 16. semiconductor has a first rectangular shape, the first area has a second rectangular shape that is smaller than the first rectangular shape and the second area has a predetermined width.
- (New) The semiconductor device according to claim 15, wherein the substrate 17. has a plurality of interconnections locating from the first area to the third area through the second area.
- (New) The semiconductor device according to claim 17, wherein the substrate 18. further has a plurality of bonding pads connected to the interconnections.
- (New) The semiconductor device according to claim 18, wherein the bonding 19. pads are located on the third area.
- (New) The semiconductor device according to claim 17, wherein the substrate 20. further has a plurality of through holes connected to the interconnections.
- (New) The semiconductor device according to claim 20, wherein the through 21. holes are located on the first area.
- (New) The semiconductor device according to claim 15, wherein the substrate 22. has a plurality of conductive terminals located on the back side of the substrate.
- (New) The semiconductor device according to claim 15, wherein the 23. conductive terminals are solder balls.